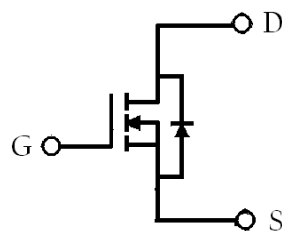


N-Channel Enhancement Mode Power MOSFET

Features:

- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package



G : Gate D : Drain S : Source

BV_{DSS}	150V
I_D@T_C=25°C, V_{GS}=10V	20.6A
R_{DS(ON)}@V_{GS}=10V, I_D=15A	46.4 mΩ(typ)
R_{DS(ON)}@V_{GS}=4.5V, I_D=10A	50.8 mΩ(typ)

TO-252(DPAK)



Ordering Information

Device	Package	Shipping
KJB050N15AR	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel

Absolute Maximum Ratings (T_C=25°C)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage (Note 1)	V _{DS}	150	V	
Gate-Source Voltage	V _{GS}	±20		
Continuous Drain Current @T _C =25°C, V _{GS} =10V (Note 1)	I _D	20.6	A	
Continuous Drain Current @T _C =100°C, V _{GS} =10V (Note 1)		14.6		
Continuous Drain Current @T _A =25°C, V _{GS} =10V (Note 2)	I _{DSM}	4.6		
Continuous Drain Current @T _A =70°C, V _{GS} =10V (Note 2)		3.8		
Pulsed Drain Current @ V _{GS} =10V	I _{DM}	60		
Single Pulse Avalanche Current @L=0.1mH (Note 3)	I _{AS}	40		
Single Pulse Avalanche Energy @ L=0.5mH, I _D =20 Amps, V _{DD} =50V (Note 5)	E _{AS}	100		mJ
Repetitive Avalanche Energy (Note 3)	E _{AR}	6		
Power Dissipation	P _D	T _C =25°C (Note 1)	60	W
		T _C =100°C (Note 1)	30	
	P _D SM	T _A =25°C (Note 2)	2.5	
		T _A =70°C (Note 2)	1.6	
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+175	°C	

*Drain current limited by maximum junction temperature

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	2.5	°C/W
Thermal Resistance, Junction-to-ambient, max (Note 2)	R _{θJA}	50	
Thermal Resistance, Junction-to-ambient, max (Note 4)		110	

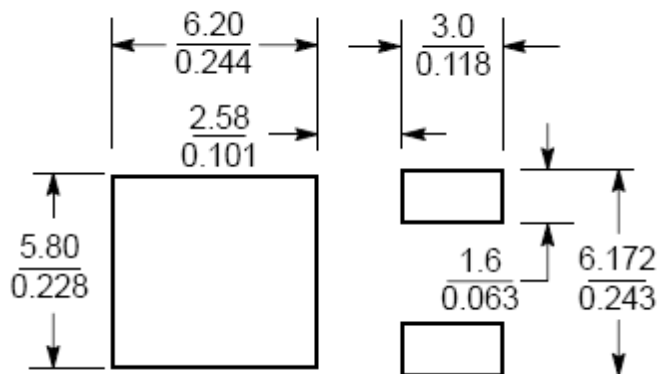
- Note : 1. The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
2. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_DSM is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.
3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.
4. When mounted on the minimum pad size recommended (PCB mount), t_≤10s.
5. 100% tested by conditions of V_{DD}=50V, L=0.1mH, V_{GS}=10V, I_{AS}=10A

Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	150	-	-	V	V _{GS} =0V, I _D =250μA
ΔBV _{DSS} /ΔT _j	-	0.13	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	1	-	2.5	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	14.5	-	S	V _{DS} =10V, I _D =10A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =120V, V _{GS} =0V
I _{DSS}	-	-	25		V _{DS} =120V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	46.4	65	mΩ	V _{GS} =10V, I _D =15A
	-	50.8	73		V _{GS} =4.5V, I _D =10A
Dynamic					
*Q _g	-	26.3	-	nC	V _{DD} =75V, I _D =15A, V _{GS} =10V
*Q _{gs}	-	4.9	-		
*Q _{gd}	-	5.9	-		
*t _{d(ON)}	-	13.6	-	ns	V _{DD} =75V, I _D =15A, V _{GS} =10V, R _G =2.5Ω
*t _r	-	18	-		
*t _{d(OFF)}	-	34.6	-		
*t _f	-	15.2	-		
C _{iss}	-	1387	-	pF	V _{GS} =0V, V _{DS} =80V, f=1MHz
C _{oss}	-	68	-		
C _{rss}	-	10	-		
R _g	-	0.9	-	Ω	f=1MHz
Source-Drain Diode					
*I _S	-	-	20	A	
*I _{SM}	-	-	60		
*V _{SD}	-	0.9	1.2	V	I _S =15A, V _{GS} =0V
*t _{rr}	-	34.6	-	ns	V _{GS} =0V, I _F =1A, dI _F /dt=100A/μs
*Q _{rr}	-	43.3	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

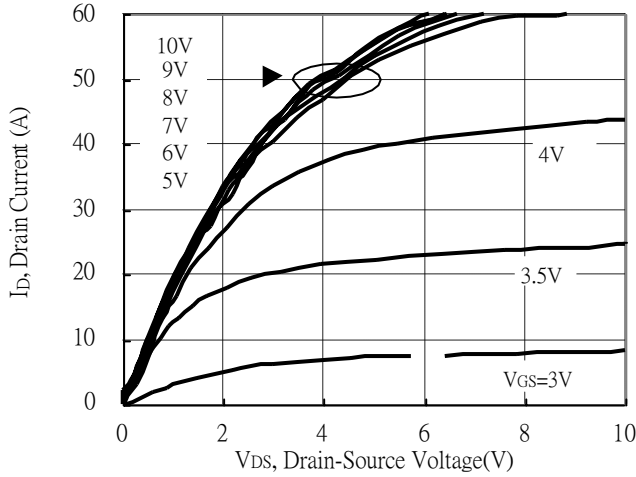
Recommended soldering footprint



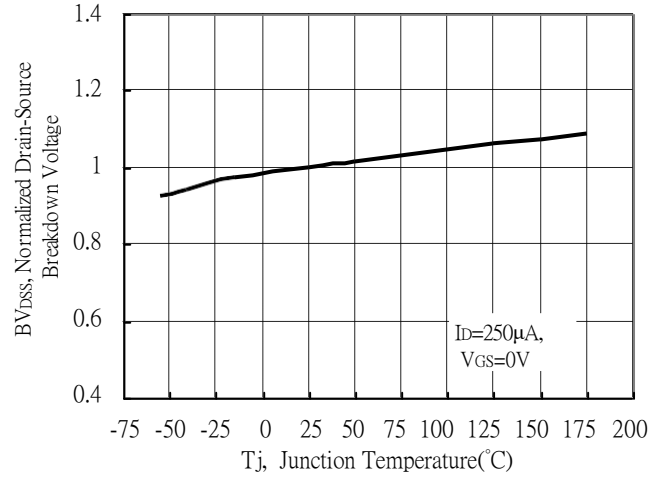
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

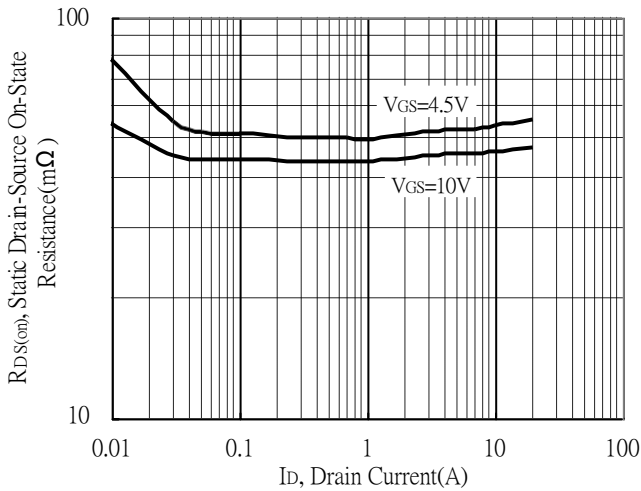
Typical Output Characteristics



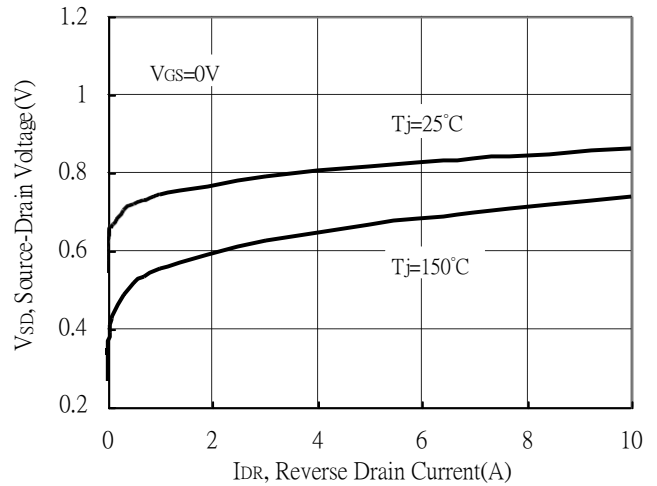
Brekdown Voltage vs Ambient Temperature



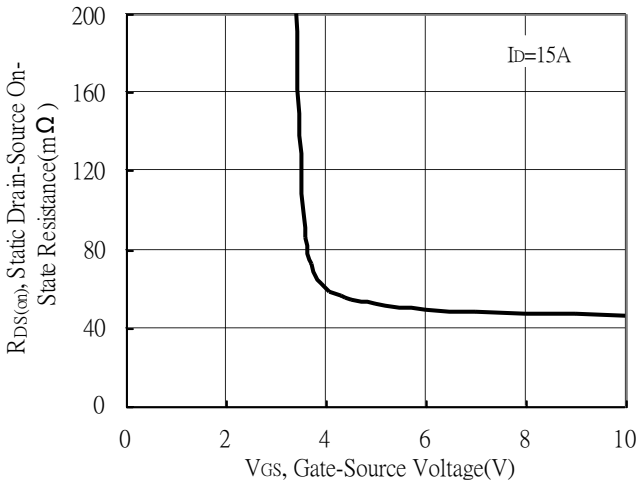
Static Drain-Source On-State resistance vs Drain Current



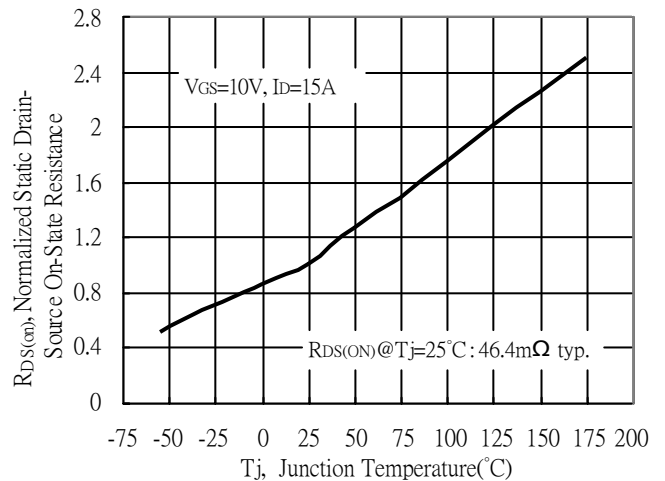
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

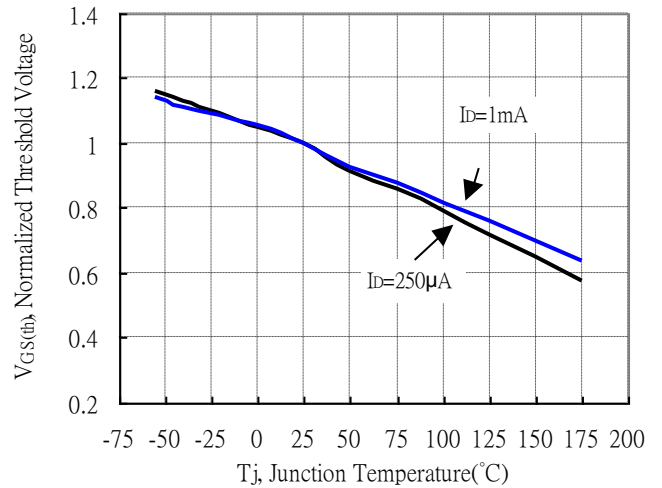
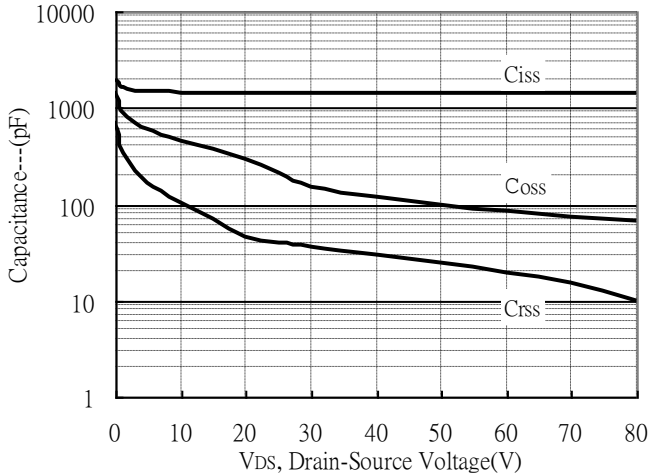


Drain-Source On-State Resistance vs Junction Temperature

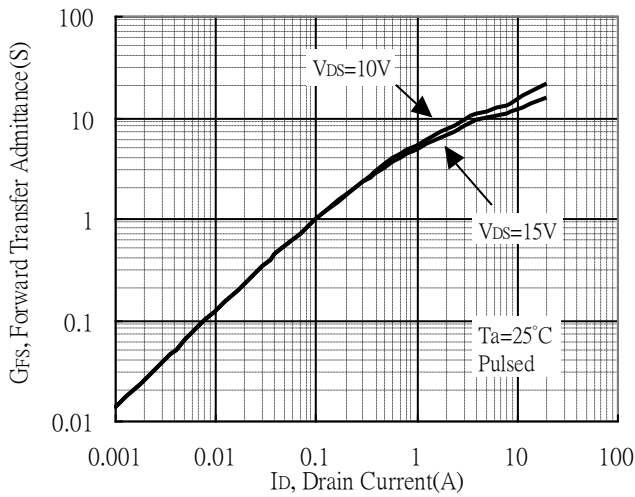


Typical Characteristics(Cont.)

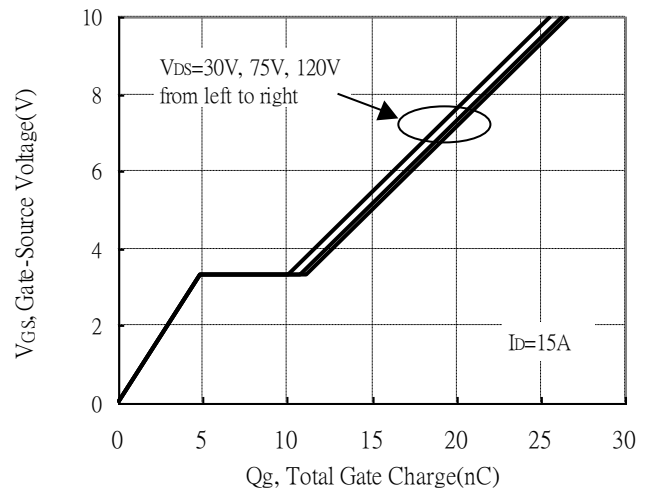
Capacitance vs Drain-to-Source Voltage



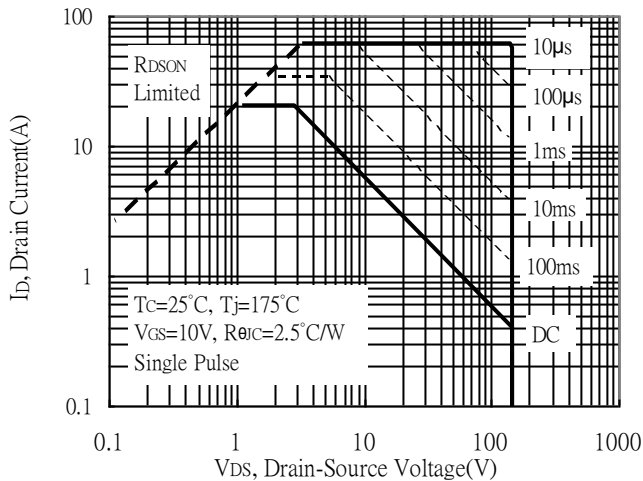
Forward Transfer Admittance vs Drain Current



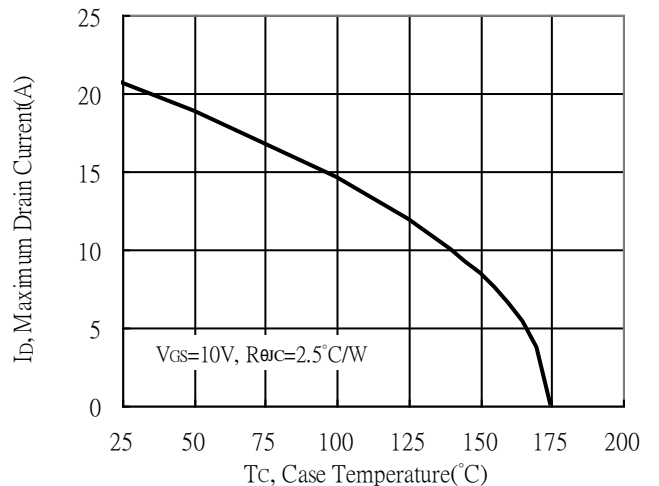
Gate Charge Characteristics



Maximum Safe Operating Area

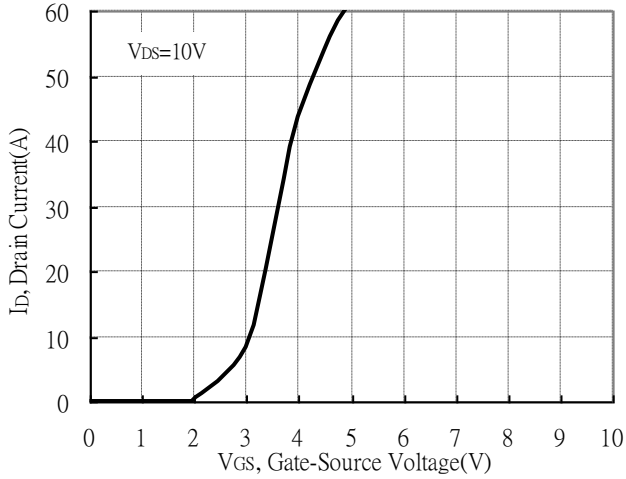


Maximum Drain Current vs Case Temperature

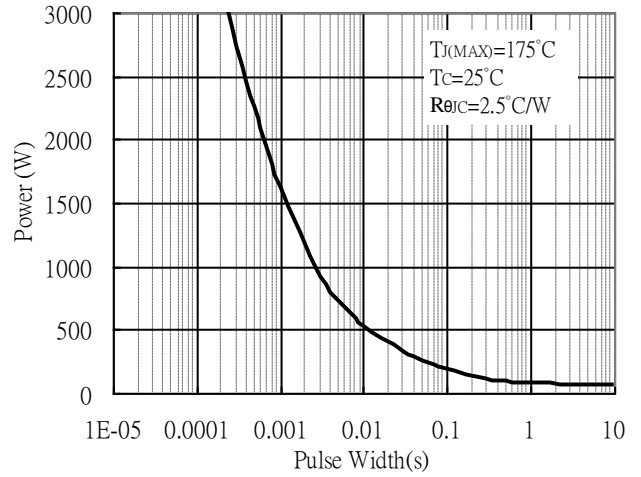


Typical Characteristics(Cont.)

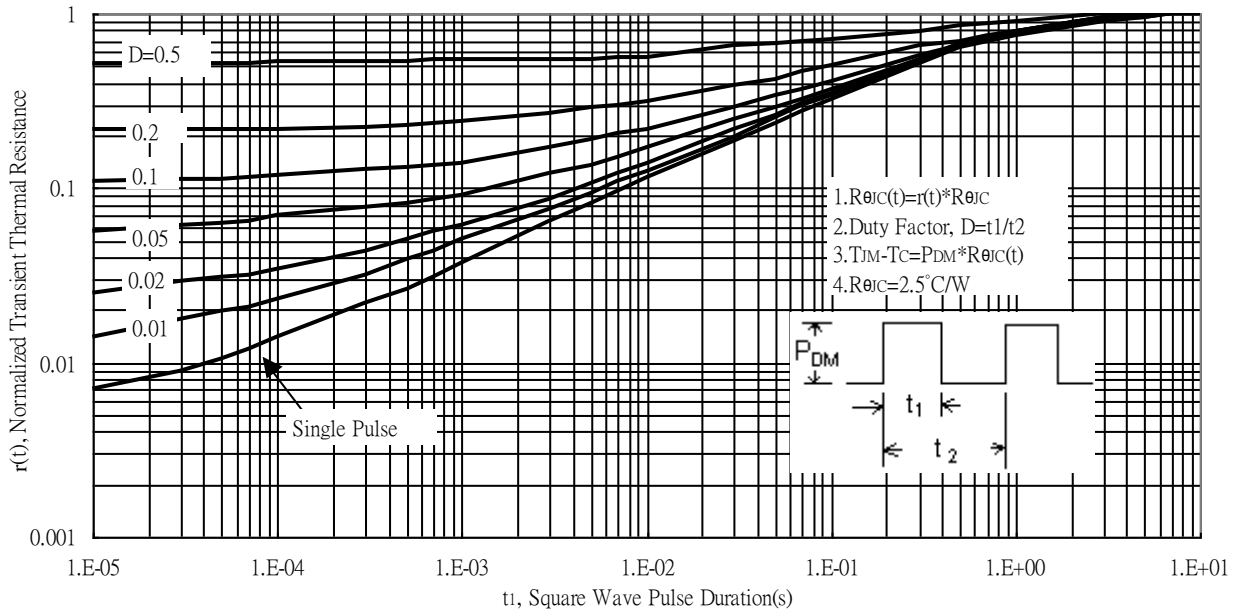
Typical Transfer Characteristics



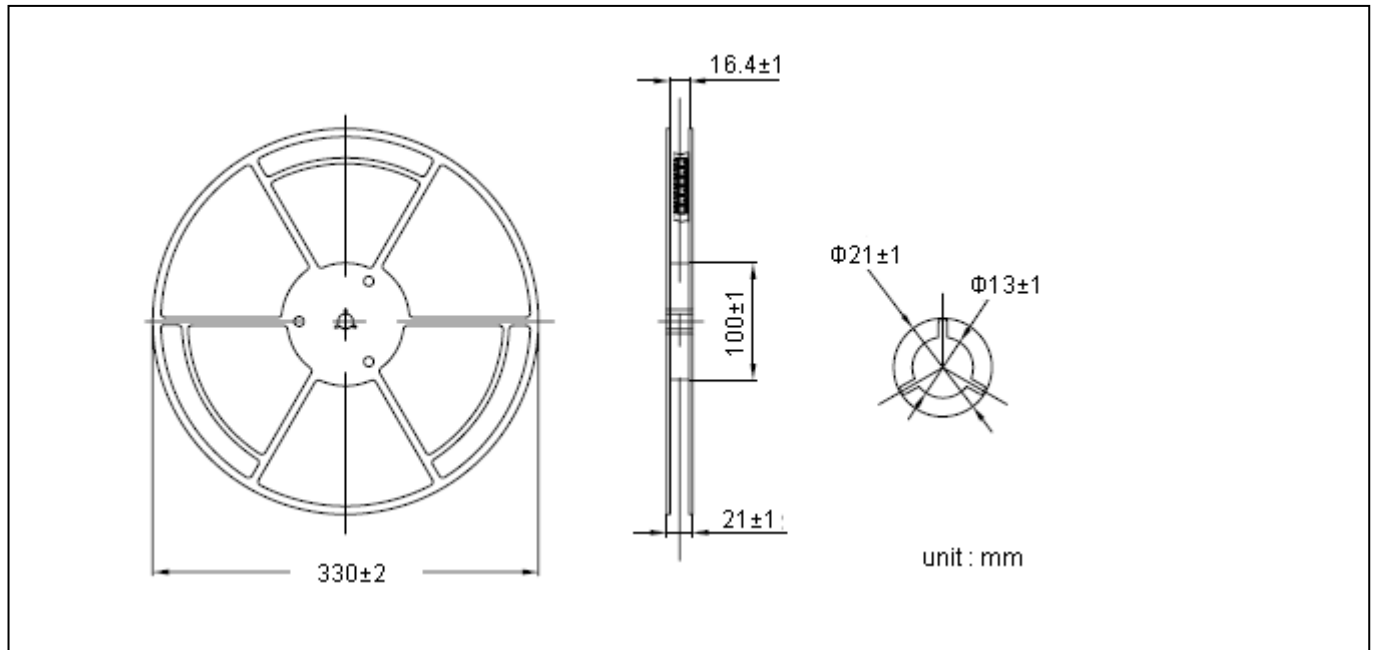
Single Pulse Power Rating, Junction to Case



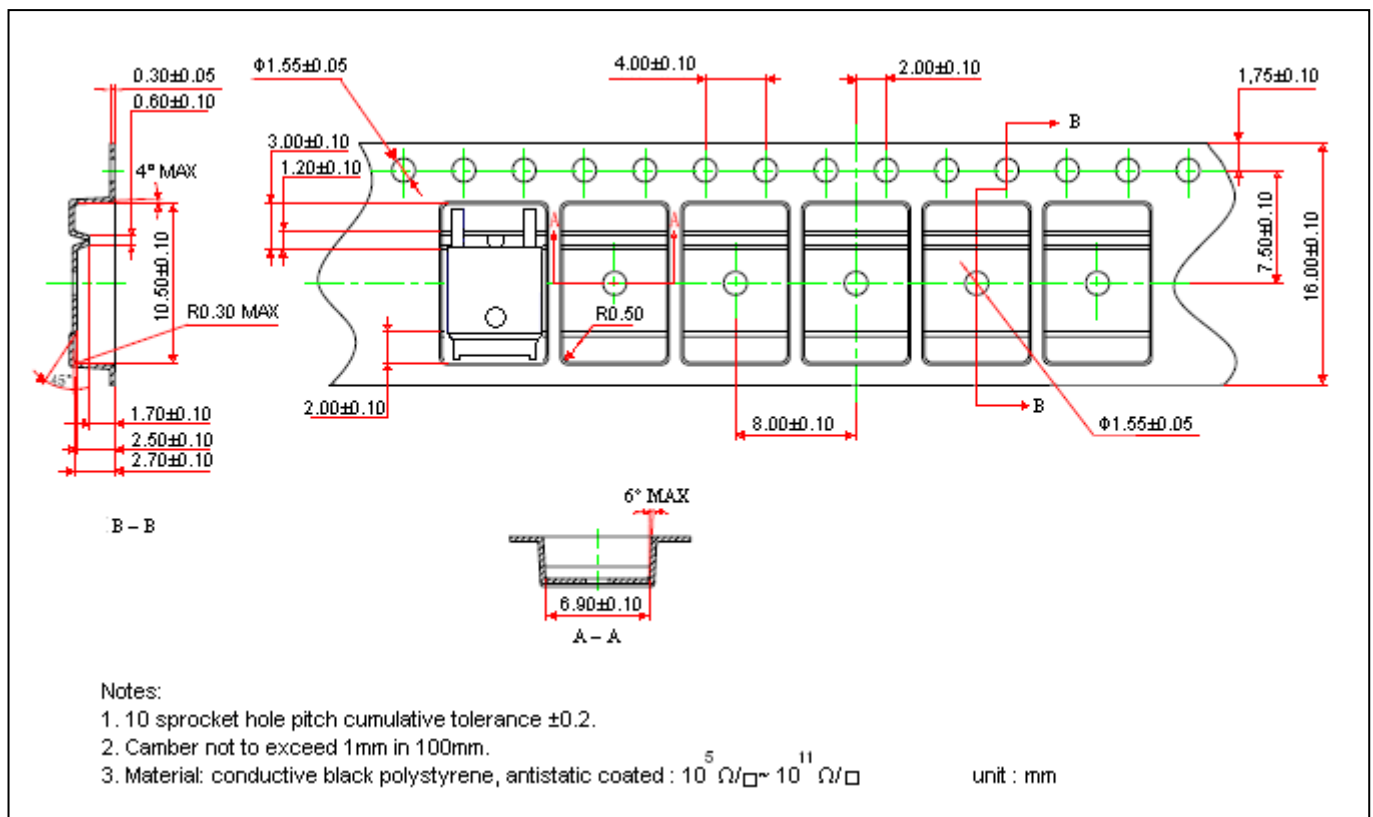
Transient Thermal Response Curves



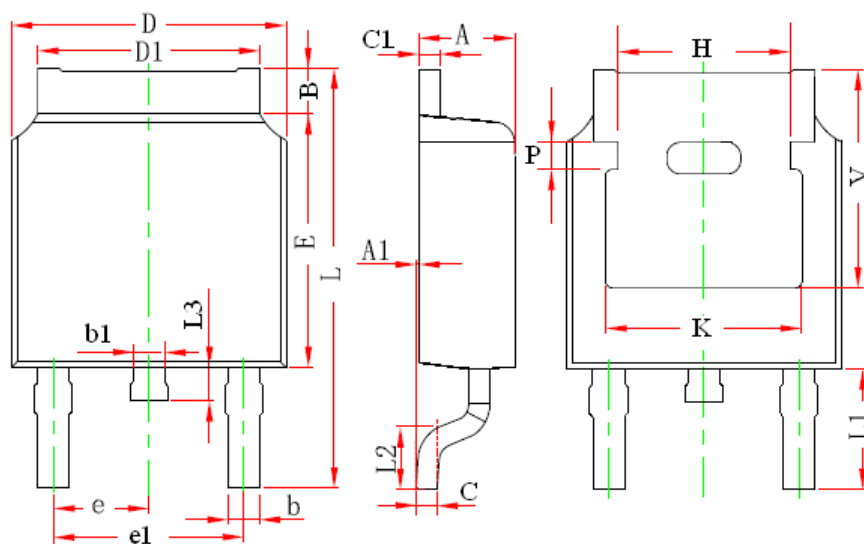
Reel Dimension



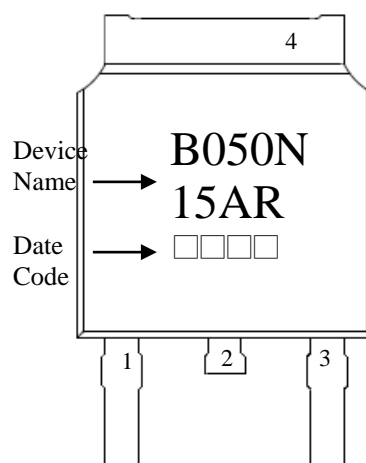
Carrier Tape Dimension



TO-252 Dimension



Marking:



3-Lead TO-252 Plastic Surface Mount Package

Style: Pin 1.Gate 2.Drain 3.Source
4.Drain

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF